

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/8150002/publications.pdf>

Version: 2024-02-01

155  
papers

1,421  
citations

331259

21  
h-index

414034

32  
g-index

157  
all docs

157  
docs citations

157  
times ranked

1587  
citing authors

#	ARTICLE	IF	CITATIONS
1	Effects of indium composition on the surface morphological and optical properties of InGaN/GaN heterostructures. <i>Microelectronics International</i> , 2023, 40, 8-16.	0.4	1
2	Anisotropy of DNA molecule detection and enhancement by GaN-based electronic sensor. <i>Optics Letters</i> , 2022, 47, 417.	1.7	0
3	Recent advances and challenges in the MOCVD growth of indium gallium nitride: A brief review. <i>Materials Science in Semiconductor Processing</i> , 2022, 143, 106545.	1.9	25
4	Analysis using a two-layer model of the transport properties of InGaN epilayers grown on GaN template substrate. <i>Materials Science in Semiconductor Processing</i> , 2022, 144, 106614.	1.9	3
5	Characterization and tuning of anisotropy property of grating structure using electrical method. <i>Optik</i> , 2022, 262, 169338.	1.4	0
6	The dependence of indium incorporation on specified temperatures in growing InGaN/GaN heterostructure using MOCVD technique. <i>Materials Research Bulletin</i> , 2021, 137, 111176.	2.7	6
7	Fabrication and characterization of InN-based metal-semiconductor-metal infrared photodetectors prepared using sol-gel spin coated technique. <i>Functional Materials Letters</i> , 2021, 14, 2151024.	0.7	1
8	The role of growth temperature on the indium incorporation process for the MOCVD growth of InGaN/GaN heterostructures. <i>Microelectronics International</i> , 2021, 38, 105-112.	0.4	1
9	Effect of pH on the Synthesis of Cobalt Selenide Films by SILAR Method. <i>Oriental Journal of Chemistry</i> , 2021, 37, 791-796.	0.1	2
10	Photostrictive behavior as the piezo-phototronic effect in InGaN/GaN multiple quantum wells. <i>Nano Energy</i> , 2021, 86, 106085.	8.2	4
11	Reactive Sputtering Growth of Indium Nitride Thin Films on Flexible Substrate Under Different Substrate Temperatures. <i>Journal of Physics: Conference Series</i> , 2020, 1535, 012029.	0.3	3
12	Reversible Circular Dichroism Induced by Energy Losses without Changing Chirality of Structure. <i>Annalen Der Physik</i> , 2020, 532, 1900539.	0.9	1
13	Multiple electromagnetically induced transparency-like effects of a metal nanostructure induced by a graphene grating deposited on a gallium oxide substrate. <i>Applied Optics</i> , 2020, 59, 7918.	0.9	3
14	Sol-Gel Spin Coating Growth of Magnesium-Doped Indium Nitride Thin Films on Different Substrates. <i>Engineering Journal</i> , 2020, 24, 285-294.	0.5	1
15	Infrared reflectance characterization of porous GaN thin films on sapphire substrate using factorized-Rayleigh model. <i>Optical Materials</i> , 2019, 96, 109320.	1.7	2
16	Influence of sulfurization temperature on the molybdenum disulfide thin films grown by thermal vapour sulfurization. <i>Materials Today: Proceedings</i> , 2019, 17, 921-928.	0.9	0
17	Effects of microwave activation power on the structural properties of sol-gel spin coated magnesium doped gallium nitride thin films. <i>Materials Today: Proceedings</i> , 2019, 16, 1673-1679.	0.9	1
18	Comparative Study of Gas Ratio on Indium Nitride Thin Films Grown on Flexible Substrates Prepared by Reactive Sputtering Method. <i>Solid State Phenomena</i> , 2019, 290, 142-146.	0.3	0

#	ARTICLE	IF	CITATIONS
19	Growth process of molybdenum disulfide thin films grown by thermal vapour sulfurization. Journal of Materials Science: Materials in Electronics, 2019, 30, 10419-10426.	1.1	2
20	UV Photodetector Based on Mg-Doped GaN Thin Films Prepared by Sol-Gel Spin Coating. Solid State Phenomena, 2019, 290, 208-213.	0.3	2
21	A systematic study on the growth of molybdenum disulfide with the carbon disulfide as the sulfurizing source. Ceramics International, 2019, 45, 13701-13710.	2.3	0
22	Influence of the substrate types on the molybdenum disulfide grown by thermal vapour sulfurization. Superlattices and Microstructures, 2019, 129, 69-76.	1.4	0
23	Sol-gel-derived gallium nitride thin films for ultraviolet photodetection. Microelectronics International, 2019, 36, 8-13.	0.4	5
24	Development of Novel Thin Film Solar Cells: Design and Numerical Optimisation. Journal of Physical Science, 2019, 30, 199-205.	0.5	2
25	Influence of initial sulfur content in precursor solution for the growth of molybdenum disulfide. Journal of Physics: Conference Series, 2018, 995, 012060.	0.3	5
26	Low-cost growth of magnesium doped gallium nitride thin films by sol-gel spin coating method. IOP Conference Series: Materials Science and Engineering, 2018, 284, 012031.	0.3	1
27	Effects of coating cycles on spin-coated indium nitride thin films. Surface Engineering, 2018, 34, 554-561.	1.1	2
28	Sol-gel spin coating growth of magnesium-doped indium nitride thin films. Vacuum, 2018, 155, 16-22.	1.6	7
29	Influences of elevated thermal decomposition of ammonia gas on indium nitride grown by sol-gel spin coating method. Materials Research Bulletin, 2017, 96, 258-261.	2.7	4
30	Growth mechanism of indium nitride via sol-gel spin coating method and nitridation process. Surface and Coatings Technology, 2017, 310, 38-42.	2.2	14
31	An investigation of GaN thin films on AlN on sapphire substrate by sol-gel spin coating method. AIP Conference Proceedings, 2017, , .	0.3	0
32	Synthesis of gallium nitride thin films using sol-gel dip coating method. AIP Conference Proceedings, 2017, , .	0.3	0
33	Doped indium nitride thin film by sol-gel spin coating method. AIP Conference Proceedings, 2017, , .	0.3	1
34	Insights on semiconductor-metal transition in indium-doped zinc oxide from x-ray photoelectron spectroscopy, time-of-flight secondary ion mass spectrometry and x-ray diffraction. AIP Conference Proceedings, 2016, , .	0.3	2
35	Infrared optical responses of wurtzite $\text{In}_x\text{Ga}_{1-x}\text{N}$ thin films with porous surface morphology. Thin Solid Films, 2016, 603, 334-341.	0.8	0
36	Influence of force constant on surface phonon polariton properties of cubic $\text{ZnS}_{1-x}\text{Se}_x$ crystals. AIP Conference Proceedings, 2015, , .	0.3	0

#	ARTICLE	IF	CITATIONS
37	Effects of sputtering power on properties of copper oxides thin films deposited on glass substrates. AIP Conference Proceedings, 2015, , .	0.3	0
38	Polarized infrared attenuated total reflection study of sapphire crystals with different crystallographic planes. AIP Conference Proceedings, 2015, , .	0.3	1
39	New Insights on the Burstein-Moss Shift and Band Gap Narrowing in Indium-Doped Zinc Oxide Thin Films. PLoS ONE, 2015, 10, e0141180.	1.1	122
40	Preparation and characterization of ZnxCd1-x ternary alloys micro/nanostructures grown by thermal evaporation. Materials Research Express, 2015, 2, 016501.	0.8	3
41	Luminescence evolution of porous GaN thin films prepared via UV-assisted electrochemical etching. Journal of Luminescence, 2015, 159, 303-311.	1.5	7
42	Effects of Nitridation Temperature on Characteristics of Gallium Nitride Thin Films Prepared Via Two-Step Method. Acta Metallurgica Sinica (English Letters), 2015, 28, 362-366.	1.5	6
43	Fabrication of titanium dioxide nanotubes in fluoride-free electrolyte via rapid breakdown anodization. Journal of Porous Materials, 2015, 22, 1437-1444.	1.3	14
44	Effect of deposition conditions on properties of nitrogen rich-InN nanostructures grown on anisotropic Si (110). Materials Science in Semiconductor Processing, 2015, 35, 216-221.	1.9	8
45	Growth of GaN on sputtered GaN buffer layer via low cost and simplified sol-gel spin coating method. Vacuum, 2015, 119, 119-122.	1.6	23
46	Growth and Characterization of AlN Thin Film Deposited by Sol-Gel Spin Coating Techniques. Advanced Materials Research, 2015, 1107, 667-671.	0.3	3
47	Ohmic-Rectifying Conversion of Ni Contacts on ZnO and the Possible Determination of ZnO Thin Film Surface Polarity. PLoS ONE, 2014, 9, e86544.	1.1	7
48	Determination of Acceptor Concentration, Depletion Width, Donor Level Movement and Sensitivity Factor of ZnO on Diamond Heterojunction under UV Illumination. PLoS ONE, 2014, 9, e89348.	1.1	7
49	Surface phonon polariton responses of hexagonal sapphire crystals with non-polar and semi-polar crystallographic planes. Optics Letters, 2014, 39, 5467.	1.7	7
50	Formation and Optical Studies of Porous GaN Thin Films via UV-Assisted Electrochemical Etching Approach. Advanced Materials Research, 2014, 895, 45-50.	0.3	1
51	Calculation of dispersion of surface and interface phonon polariton resonances in wurtzite semiconductor multilayer system taking damping effects into account. Thin Solid Films, 2014, 551, 114-119.	0.8	5
52	Polarized infrared reflectance study of free standing cubic GaN grown by molecular beam epitaxy. Materials Chemistry and Physics, 2014, 146, 121-128.	2.0	4
53	Synthesis of wurtzite GaN thin film via spin coating method. Materials Science in Semiconductor Processing, 2014, 17, 63-66.	1.9	22
54	Crystal orientation dependence of polarized infrared reflectance response of hexagonal sapphire crystal. Optical Materials, 2014, 37, 773-779.	1.7	11

#	ARTICLE	IF	CITATIONS
55	Effects of nitridation durations on the synthesis of wurtzite GaN thin films by spin coating method. Journal of Sol-Gel Science and Technology, 2014, 71, 329-332.	1.1	8
56	Solvothermal growth of single-crystal CdS nanowires. Bulletin of Materials Science, 2014, 37, 337-345.	0.8	10
57	Optical properties of CdS micro/nanocrystalline structures prepared via a thermal evaporation method. Materials Science in Semiconductor Processing, 2014, 26, 87-92.	1.9	24
58	Effect of annealing temperature on IR-detectors based on InN nanostructures. Vacuum, 2014, 106, 46-48.	1.6	13
59	Structural and optical properties of In-doped ZnO thin films under wet annealing. Materials Letters, 2014, 116, 396-398.	1.3	14
60	Photoluminescence spectra of nitrogen-rich InN thin films grown on Si(110) and photoelectrochemical etched Si(110). Vacuum, 2014, 101, 217-220.	1.6	12
61	Effects of oxygen percentage on the growth of copper oxide thin films by reactive radio frequency sputtering. Materials Chemistry and Physics, 2013, 140, 243-248.	2.0	47
62	Infrared reflectance studies of hillock-like porous zinc oxide thin films. Thin Solid Films, 2013, 539, 70-74.	0.8	3
63	Synthesis of two-dimensional gallium nitride via spin coating method: influences of nitridation temperatures. Journal of Sol-Gel Science and Technology, 2013, 68, 95-101.	1.1	17
64	Growth and characterization of CdS single-crystalline micro-rod photodetector. Superlattices and Microstructures, 2013, 54, 137-145.	1.4	40
65	Synthesis of nanocrystalline In <sub>2</sub> O <sub>3</sub> on different Si substrates at wet oxidation environment. Optik, 2013, 124, 2679-2681.	1.4	6
66	Influence of post-annealing condition on the properties of ZnO films. Ceramics International, 2013, 39, S263-S267.	2.3	9
67	Substrate surface polariton splitting due to thin zinc oxide and aluminum nitride films presence. Applied Surface Science, 2013, 267, 93-96.	3.1	4
68	Surface and optical phonon characteristics of ZnO/diamond heterostructure. Ceramics International, 2013, 39, S529-S532.	2.3	1
69	Optical and structural properties of porous zinc oxide fabricated via electrochemical etching method. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2013, 178, 956-959.	1.7	6
70	Structural and morphological properties of zinc oxide thin films grown on silicon substrates. , 2013, , .		0
71	Fabrication of porous ZnO via electrochemical etching using 10wt% potassium hydroxide solution. Materials Science in Semiconductor Processing, 2013, 16, 70-76.	1.9	12
72	Polarized infrared reflectance characterization of wurtzite ZnO/GaN heterostructure on 6H-SiC substrate. , 2013, , .		1

#	ARTICLE	IF	CITATIONS
73	Fabrication and characterization of macroporous zinc oxide. , 2013, , .		0
74	Comparative study on structural and optical properties of nitrogen rich InN on Si(110) and 6H-SiC. Surface Engineering, 2013, 29, 561-565.	1.1	11
75	Growth of InN thin films on different Si substrates at ambient temperature. Microelectronics International, 2013, 30, 63-67.	0.4	8
76	Fabrication of InN based photodetector using porous silicon buffer layer. Surface Engineering, 2013, 29, 772-777.	1.1	15
77	Ultraviolet Photoresponse Properties of Zinc Oxide Nanorods on Heavily Boron-Doped Diamond Heterostructure. Advanced Materials Research, 2013, 832, 172-177.	0.3	1
78	STRUCTURE AND OPTICAL PROPERTIES OF $\text{InN}$ THIN FILM GROWN ON $\text{SiC}$ BY REACTIVE RF MAGNETRON SPUTTERING. Surface Review and Letters, 2013, 20, 1350008.	0.5	9
79	Surface phonon polariton characteristic of honeycomb nanoporous GaN thin films. Applied Physics Letters, 2013, 102, 101601.	1.5	17
80	$\text{InN}$ PHOTOCONDUCTORS ON DIFFERENT ORIENTATIONS OF $\text{Si}$ SUBSTRATES. International Journal of Modern Physics B, 2012, 26, 1250137.	1.0	9
81	Reactive Sputtering Growth and Characterizations of InN Thin Films on Si Substrates. Advanced Materials Research, 2012, 545, 290-293.	0.3	0
82	Fabrication of porous ZnO thin films using wet chemical etching with 0.5% HNO <sub>3</sub> . Microelectronics International, 2012, 29, 96-100.	0.4	3
83	Optical properties of photo-electrochemical etching of anisotropic silicon (110). IEICE Electronics Express, 2012, 9, 752-757.	0.3	6
84	Growth and characterization of $\text{ZnxCd}_{1-x}\text{S}$ nanoflowers by microwave-assisted chemical bath deposition. Journal of Alloys and Compounds, 2012, 541, 227-233.	2.8	38
85	Synthesis and characterization of single-crystal CdS nanosheet for high-speed photodetection. Physica E: Low-Dimensional Systems and Nanostructures, 2012, 44, 1716-1721.	1.3	67
86	Growth of CdS nanosheets and nanowires through the solvothermal method. Journal of Crystal Growth, 2012, 359, 43-48.	0.7	44
87	EFFECT OF CURRENT DENSITY ON OPTICAL PROPERTIES OF ANISOTROPIC PHOTOELECTROCHEMICAL ETCHED SILICON (110). Modern Physics Letters B, 2012, 26, 1250131.	1.0	5
88	Surface phonon polariton characteristics of wurtzite ZnO thin film grown on silicon substrate. Physica Status Solidi (B): Basic Research, 2012, 249, 1058-1062.	0.7	2
89	Surface phonon polariton of wurtzite AlN thin film grown on sapphire. Materials Chemistry and Physics, 2012, 134, 493-498.	2.0	5
90	Structural and optical properties of nanocrystalline CdS thin films prepared using microwave-assisted chemical bath deposition. Thin Solid Films, 2012, 520, 3477-3484.	0.8	97

#	ARTICLE	IF	CITATIONS
91	Structural, optical and electrical properties of europium picrate tetraethylene glycol complex as emissive material for OLED. Journal of Luminescence, 2012, 132, 91-99.	1.5	8
92	Photoluminescence and XRD Crystalline Studies of In <sub>x</sub> Al <sub>y</sub> Ga <sub>1-x-y</sub> N Quaternary Alloys. IOP Conference Series: Materials Science and Engineering, 2011, 17, 012006.	0.3	1
93	Surface and interface phonon polariton characteristics of wurtzite ZnO/GaN heterostructure. Applied Physics Letters, 2011, 98, 241909.	1.5	8
94	Far Infrared Optical Properties of Bulk Wurtzite Zinc Oxide Semiconductor. Journal of Materials Science and Technology, 2011, 27, 465-470.	5.6	10
95	Polarized infrared reflectance studies for wurtzite InN epilayers on Si(111) grown by molecular beam epitaxy. Thin Solid Films, 2011, 520, 739-742.	0.8	5
96	Effect of Al mole fraction on structural and electrical properties of Al <sub>x</sub> Ga <sub>1-x</sub> N/GaN heterostructures grown by plasma-assisted molecular beam epitaxy. Applied Surface Science, 2011, 257, 4159-4164.	3.1	21
97	Characterization of Al <sub>x</sub> In <sub>y</sub> Ga <sub>1-x-y</sub> N quaternary alloys grown on sapphire substrates by molecular-beam epitaxy. Materials Science in Semiconductor Processing, 2011, 14, 164-169.	1.9	3
98	Surface phonon polariton characteristics of bulk wurtzite ZnO crystal. Physica B: Condensed Matter, 2011, 406, 115-118.	1.3	6
99	Experimental investigation of long-wavelength optical lattice vibrations in quaternary Al <sub>x</sub> In <sub>y</sub> Ga <sub>1-x-y</sub> N alloys and comparison with results from the pseudo-unit cell model. Physica B: Condensed Matter, 2011, 406, 1379-1384.	1.3	5
100	Studies of surface and interface phonon polariton characteristics of wurtzite ZnO thin film on wurtzite 6H-SiC substrate by p-polarized infrared attenuated total reflection spectroscopy. Thin Solid Films, 2011, 519, 3703-3708.	0.8	12
101	Theoretical studies of surface phonon polariton in wurtzite AlInN ternary alloy. Thin Solid Films, 2011, 519, 5481-5485.	0.8	8
102	Photoluminescence Characterization of ZnO Thin Films Grown by RF- Sputtering. , 2011, , .		0
103	Strong Room Temperature 505 nm Emission from Hexagonal Crack Free InGaN Thin Film on Si(111) Grown by MBE. Composite Interfaces, 2011, 18, 37-47.	1.3	1
104	Dispersion of Surface and Interface Phonon Polariton Modes in Wurtzite Based Multilayer System. Journal of the Physical Society of Japan, 2011, 80, 084712.	0.7	9
105	X-ray diffraction studies of Al <sub>x</sub> Ga <sub>1-x</sub> N (0 ≤ x ≤ 1) ternary alloys grown on sapphire substrate. Microelectronics International, 2011, 28, 44-48.	0.4	1
106	Characterizations of InN Thin Films Grown on Si (110) Substrate by Reactive Sputtering. Journal of Nanomaterials, 2011, 2011, 1-7.	1.5	26
107	Structural Properties Studies of Zinc Oxide Thin Film Grown on Silicon Carbide by Means of X-ray Diffraction Technique. , 2011, , .		0
108	p-polarized infrared attenuated total reflection study of InN thin films grown on Si(111) substrate. Physica Status Solidi - Rapid Research Letters, 2010, 4, 191-193.	1.2	2

#	ARTICLE	IF	CITATIONS
109	Ultraviolet photoresponse properties of zinc oxide on type IIb diamond heterojunction. <i>Physica B: Condensed Matter</i> , 2010, 405, 4123-4127.	1.3	8
110	Structural Properties Studies of GaN on 6H-SiC by Means of X-Ray Diffraction Technique. <i>Advanced Materials Research</i> , 2010, 173, 40-43.	0.3	0
111	The Effects of Thermal Treatments on Microstructure Phosphorus-Doped ZnO Layers Grown by Thermal Evaporation. <i>Composite Interfaces</i> , 2010, 17, 863-872.	1.3	5
112	XRD Analyses of $\text{In}_{0.10}\text{Al}_x\text{Ga}_{0.90-x}\text{N}$ ( $0 \leq x \leq 0.20$ ) Quaternary Alloys. , 2010, , .		0
113	Polarized Infrared Reflectance Studies of Quaternary $\text{In}_{0.04}\text{Al}_{0.06}\text{Ga}_{0.90}\text{N}$ . , 2010, , .		0
114	Thermal Degradation of Single Crystal Zinc Oxide and the Growth of Nanostructures. , 2010, , .		0
115	Polarized Infrared Reflectance Study of InGaN Semiconductor. , 2010, , .		0
116	Determination of the Al Composition of $\text{Al}_x\text{Ga}_{1-x}\text{N}$ Thin Films By Means Of EDX and XRD Techniques. , 2010, , .		1
117	Structural and optical properties of $\text{Al}_x\text{In}_y\text{Ga}_{1-x-y}\text{N}$ quaternary alloys grown on sapphire substrates by molecular beam epitaxy. <i>Microelectronics International</i> , 2010, 27, 148-153.	0.4	1
118	Surface phonon polariton characteristics of $\text{In}_{0.04}\text{Al}_{0.06}\text{Ga}_{0.90}\text{N}/\text{AlN}/\text{Al}_{2}\text{O}_3$ heterostructure. <i>Optics Express</i> , 2010, 18, 10354.	1.7	4
119	The Study of Energy Band Gap of $\text{Al}_x\text{In}_y\text{Ga}_{1-x-y}\text{N}$ Quaternary Alloys Using UV-VIS Spectroscopy. , 2010, , .		1
120	Sapphire surface polariton splitting due to resonance with aluminum nitride film phonon. <i>Journal of Physics: Conference Series</i> , 2010, 210, 012027.	0.3	6
121	Kramers-Kronig Analysis of Infrared Reflectance Spectra for Quaternary $\text{In}_x\text{Al}_y\text{Ga}_{1-x-y}\text{N}$ Alloy. <i>AIP Conference Proceedings</i> , 2010, , .	0.3	2
122	SURFACE PHONON POLARITON MODES OF WURTZITE STRUCTURE InN SEMI-INFINITE CRYSTAL. <i>Surface Review and Letters</i> , 2009, 16, 355-358.	0.5	6
123	Surface and interface phonon polaritons of wurtzite GaN thin film grown on 6H-SiC substrate. <i>Applied Physics Letters</i> , 2009, 94, .	1.5	26
124	Structural Properties of Doped GaN on Si(111) Studied by X-Ray Diffraction Techniques. <i>Journal of Nondestructive Evaluation</i> , 2009, 28, 125-130.	1.1	23
125	Strong coupling of sapphire surface polariton with aluminum nitride film phonon. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 2009, 373, 2382-2384.	0.9	13
126	Porous Si(111) and Si(100) as an intermediate buffer layer for nanocrystalline InN films. <i>Journal of Alloys and Compounds</i> , 2009, 479, L54-L58.	2.8	30



#	ARTICLE	IF	CITATIONS
127	High Al-content Al <sub>x</sub> Ga <sub>1-x</sub> N epilayers grown on Si substrate by plasma-assisted molecular beam epitaxy. Journal of Alloys and Compounds, 2009, 487, 24-27.	2.8	51
128	The Study of Energy Band Gap of In <sub>x</sub> Al <sub>y</sub> Ga <sub>1-x-y</sub> N Quaternary Alloys using UV-VIS Spectroscopy. , 2009, , .		3
129	Surface phonon polariton of wurtzite GaN thin film grown on -plane sapphire substrate. Solid State Communications, 2008, 145, 535-538.	0.9	23
130	Composition Dependence of Surface Phonon Polariton Mode in Wurtzite In <sub>x</sub> Ga <sub>1-x</sub> N (0 ≤ x ≤ 1) Ternary Alloy. Chinese Physics Letters, 2008, 25, 4378-4380.	1.3	6
131	Effect of zinc on the growth mechanism of zinc oxide nanostructures in the nitrogen environment. Journal Physics D: Applied Physics, 2008, 41, 055506.	1.3	4
132	Experimental and theoretical studies of surface phonon polariton of AlN thin film. Applied Physics Letters, 2007, 90, 081902.	1.5	37
133	Surface phonon polariton mode of wurtzite structure Al <sub>x</sub> Ga <sub>1-x</sub> N (0 ≤ x ≤ 1) thin films. Applied Physics Letters, 2007, 91, .	1.5	21
134	High carrier concentrations of n- and p-doped GaN on Si(111) by nitrogen plasma-assisted molecular-beam epitaxy. Journal of Materials Research, 2007, 22, 2623-2630.	1.2	15
135	Polarized infrared reflectance study of wurtzite GaN thin film: The effects of angle of incidence on the optical phonon modes. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2007, 25, 1557-1561.	0.9	4
136	Porous GaN prepared by UV assisted electrochemical etching. Thin Solid Films, 2007, 515, 3469-3474.	0.8	48
137	AlGa <sub>x</sub> N metal-semiconductor-metal structure for pressure sensing applications. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 2287-2290.	0.8	1
138	Crystallinity Studies of GaN/Si Films Grown by MOCVD at Various Substrate Temperatures Using XRD. Materials Science Forum, 2006, 517, 69-72.	0.3	0
139	Effect of hydrostatic pressure on the barrier height of Ni Schottky contacts on n-AlGa <sub>x</sub> N. Applied Physics Letters, 2006, 88, 022109.	1.5	21
140	The Energy Band Gap of Al <sub>x</sub> Ga <sub>1-x</sub> N Thin Films as a Function of Al-Mole Fraction. , 2006, , .		1
141	Crystallinity studies of GaN/Si films grown at different temperatures by infrared reflectance spectroscopy. Materials Chemistry and Physics, 2005, 91, 404-408.	2.0	7
142	Optical Properties of GaN on Si Substrate Using Plasma-Assisted MOCVD Technique in the Infrared and Visible Regions. Materials Science Forum, 2005, 480-481, 519-524.	0.3	0
143	Growth and Properties of GaN/Si Heterojunction. Materials Science Forum, 2005, 480-481, 531-536.	0.3	0
144	A Simple Method to Prepare Indium Oxide Nanoparticles on Si (110). Advanced Materials Research, 0, 620, 193-197.	0.3	1

#	ARTICLE	IF	CITATIONS
145	Effect of In Concentration on the Optical Lattice Vibrations in Quaternary Al <sub>x</sub> In <sub>y</sub> Ga <sub>1-x-y</sub> N Alloys. Advanced Materials Research, 0, 501, 281-285.	0.3	0
146	Effects of Nitridation Temperatures on Gallium Nitride Thin Films Formed on Silicon Substrates. Advanced Materials Research, 0, 895, 57-62.	0.3	0
147	Spin Coating Deposition of <i>c</i> -Oriented Wurtzite Gallium Nitride Thin Film. Applied Mechanics and Materials, 0, 699, 70-75.	0.2	0
148	Characteristics of Cuprous Oxide Thin Films Deposited on Glass and Polyethylene Terephthalate Substrates. Advanced Materials Research, 0, 895, 29-34.	0.3	0
149	Characterizations of Nitrogen Doped Cupric Oxide Thin Films Deposited on Different Substrates for Solar Cell Applications. Advanced Materials Research, 0, 925, 469-473.	0.3	3
150	Theoretical Studies on Optical Phonon and Surface Phonon Polariton of Wurtzite AlInN Alloys. Advanced Materials Research, 0, 1107, 565-570.	0.3	0
151	Attenuated Total Reflection Studies of Honeycomb Nanoporous GaN Thin Films. Advanced Materials Research, 0, 1108, 9-14.	0.3	0
152	Radio-Frequency Sputtering Growth of Indium Nitride Thin Film on Flexible Substrate. Materials Science Forum, 0, 846, 650-656.	0.3	2
153	Aluminum Nitride Thin Films Grown by Sol-Gel Spin Coating Technique. Solid State Phenomena, 0, 290, 137-141.	0.3	2
154	Growth Temperature Dependence of Sol-Gel Spin Coated Indium Nitride Thin Films. Solid State Phenomena, 0, 290, 153-159.	0.3	2
155	Electrostatic Contribution to the Photo-Assisted Piezoresponse Force Microscopy by Photo-Induced Surface Charge. Microscopy and Microanalysis, 0, , 1-5.	0.2	0